

MSF10N65

N-Channel 650V MOSFET

Description

The MSF10N65 is a N-channel enhancement-mode MOSFET, providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness. The ITO-220AB package is universally preferred for all commercial-industrial applications

Features

- Low On Resistance
- Simple Drive Requirement
- Low Gate Charge
- Fast Switching Characteristic
- RoHS compliant package

Application

- Power Factor Correction
- LCD TV Power
- Full and Half Bridge Power

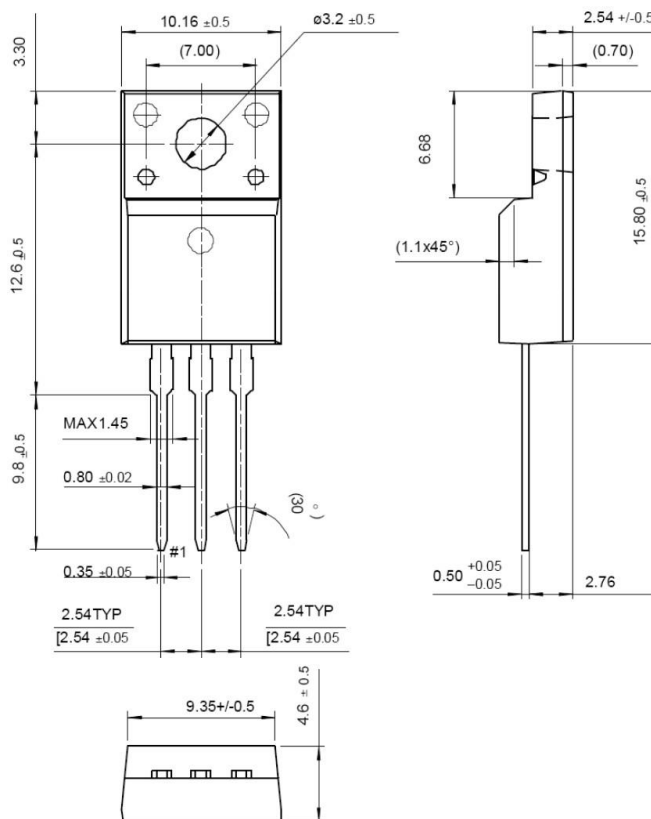
Package type : ITO220-AB

Packing & Order Information

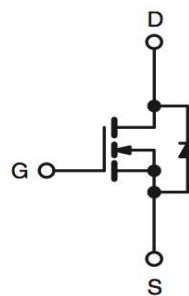
50/Tube ; 1,000/Box



**RoHS
COMPLIANT**



Graphic symbol



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{DS}	Drain-Source Voltage	650	V
V _{GS}	Gate-Source Voltage	±30	V
I _D	Drain Current -Continuous (TC=25°C)	10	A
	Drain Current -Continuous (TC=100°C)	6.0	A
I _{DM}	Drain Current Pulsed	40	A
E _{AS}	Single Pulsed Avalanche Energy	710	mJ
I _{AR}	Avalanche Current	10	A
E _{AR}	Repetitive Avalanche Energy	16.2	mJ
dV/dt	Peak Diode Recovery dV/dt	4.5	V/ns

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Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
P _D	Power Dissipation (TC = 25 °C)	52	W
	Power Dissipation (TC=100°C)	0.42	W/°C
T _J ,T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C

NOTE:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L=13mH, I_{AS}=10.0A, V_{DD}=50V, R_G=25Ω, Starting T_J=25°C
3. ISD ≤ 10.0A, di/dt ≤ 200A/μs, V_{DD} ≤ B_VD_{SS}, Starting T_J = 25°C
4. Pulse test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating temperature

Thermal characteristics (Tc=25°C unless otherwise noted)

Symbol	Parameter	Max.	Units
R _{θJC}	Junction-to-Case	2.25	°C/W
R _{θJA}	Junction-to-Ambient	62.5	

On Characteristics

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
V _{GS}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	3.0	--	5.0	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =3A	--	1.95	2.4	Ω

Off Characteristics

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
B _V D _{SS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _D =250μA	900	--	--	V
ΔB _V D _{SS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D =250μA, Referenced to 25°C	--	1.03	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =900V, V _{GS} = 0 V V _{DS} =720V, T _C = 125°C	--	--	10 100	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} =30V, V _{DS} =0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} =-30V, V _{DS} =0 V	--	--	-100	nA

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
C _{ISS}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	--	1500	2010	pF
C _{OSS}	Output Capacitance		--	145	190	pF
C _{RSS}	Reverse Transfer Capacitance		--	15	20	pF

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Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
$t_{d(on)}$	Turn-On Time	$V_{DS}=450\text{ V}, I_D=6\text{ A},$ $R_G=25\Omega$	--	40	80	ns
t_r	Turn-On Time		--	120	240	ns
$t_{d(off)}$	Turn-Off Delay Time		--	60	120	ns
t_f	Turn-Off Fall Time		--	70	140	ns
Q_g	Total Gate Charge	$V_{DS}=720\text{ V}, I_D=6\text{ A},$ $V_{GS}=10\text{ V}$	--	33	45	nC
Q_{gs}	Gate-Source Charge		--	10	--	nC
Q_{gd}	Gate-Drain Charge		--	13	--	nC

Source-Drain Diode Maximum Ratings and Characteristics						
Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
I_S	Continuous Source-Drain Diode Forward Current		--	--	6.0	A
I_{SM}	ISM Pulsed Source-Drain Diode Forward Current		--	--	24.0	
V_{SD}	Source-Drain Diode Forward Voltage	$I_S=6\text{ A}, V_{GS}=0\text{ V}$	--	--	1.4	V
t_{rr}	Reverse Recovery Time	$I_S=6\text{ A}, V_{GS}=0\text{ V}$ $diF/dt=100\text{ A}/\mu\text{ s}$	--	780	--	ns
Q_{rr}	Reverse Recovery Charge		--	9.0	--	$\mu\text{ C}$

Notes ;

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L=34\text{ mH}, I_{AS}=6\text{ A}, V_{DD}=50\text{ V}, R_G=25\Omega$, Starting $T_J=25^\circ\text{ C}$
3. $I_{SD}\leq 6\text{ A}, di/dt\leq 200\text{ A}/\mu\text{ s}, V_{DD}\leq BV_{DSS}$, Starting $T_J=25^\circ\text{ C}$
4. Pulse Test: Pulse Width $\leq 300\ \mu\text{ s}$, Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature

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■ Characteristics Curve

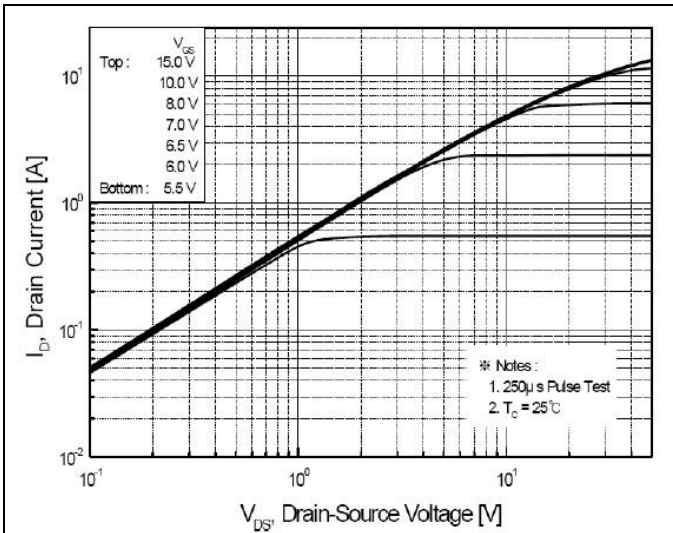


FIG.1-ON REGION CHARACTERISTICS

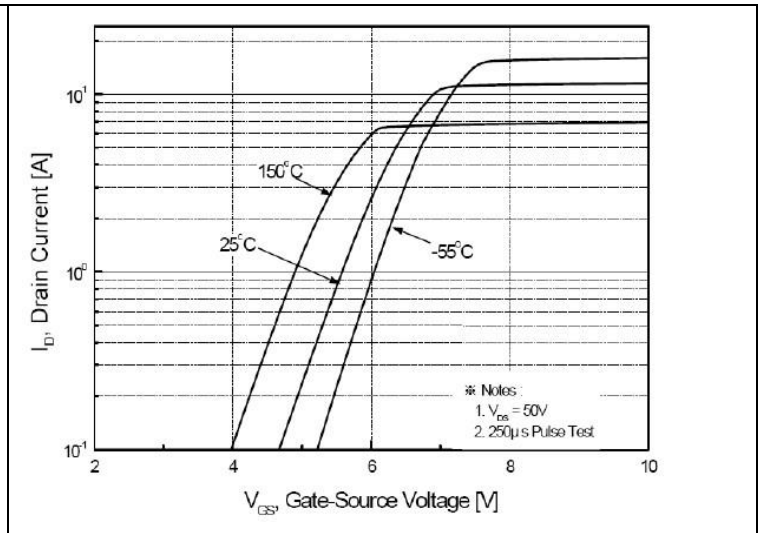


FIG.2-TRANSFER CHARACTERISTICS

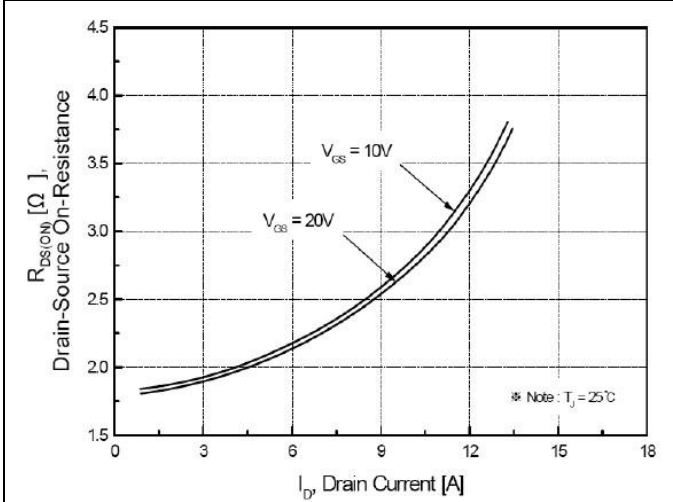


FIG.3-ON RESISTANCE VARIATION VS DRAIN CURRENT AND GATE VOLTAGE

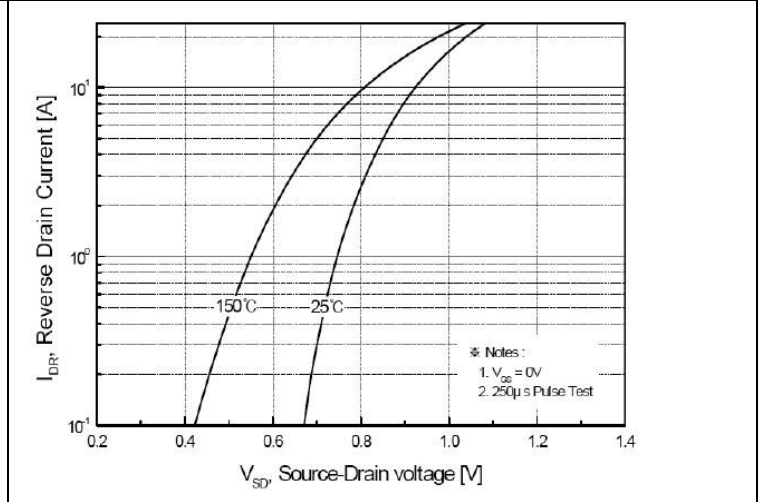


FIG.4-BODY DIODE FORWARD VOLTAGE VARIATION WITH SOURCE CURRENT AND TEMPERATURE

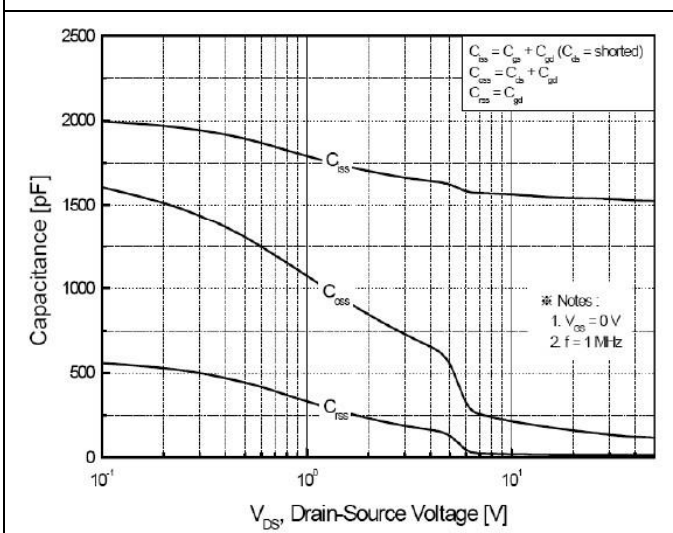


FIG.5-CAPACITANCE CHARACTERISTICS

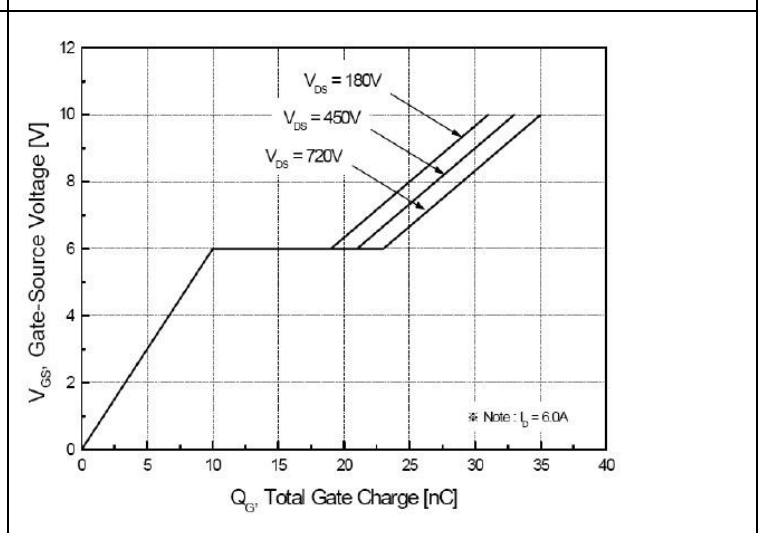


FIG.6-GATE CHARGE CHARACTERISTICS

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■ Characteristics Curve

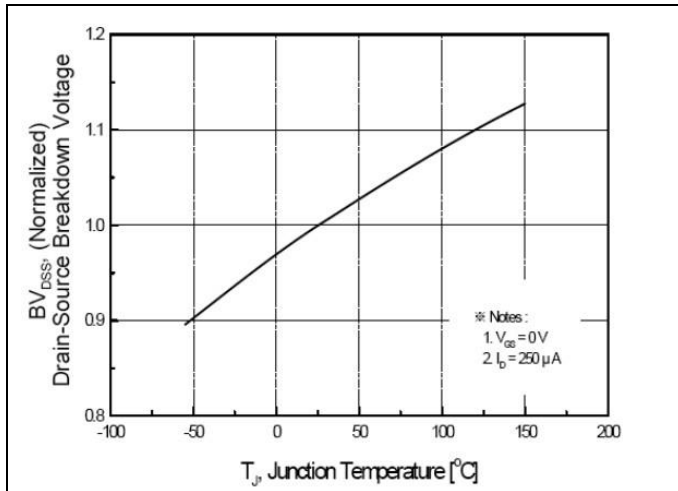


FIG.7-BREAKDOWN VOLTAGE VARIATION VS TEMPERATURE

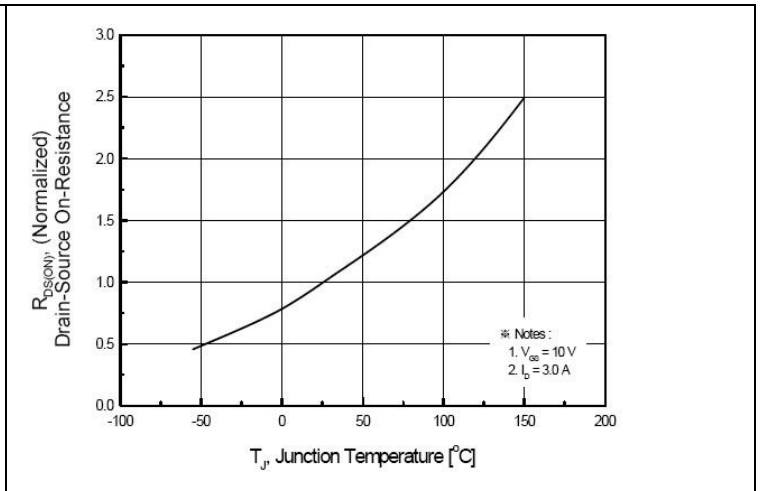


FIG.8-ON-RESISTANCE VARIATION VS TEMPERATURE

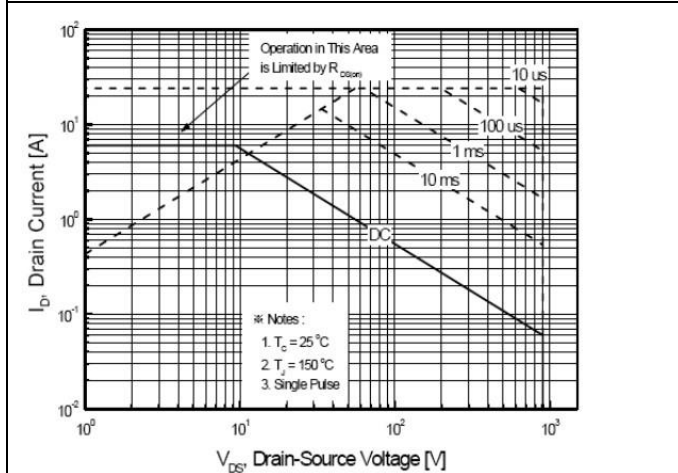


FIG.9-MAXIMUM SAFE OPERATING AREA

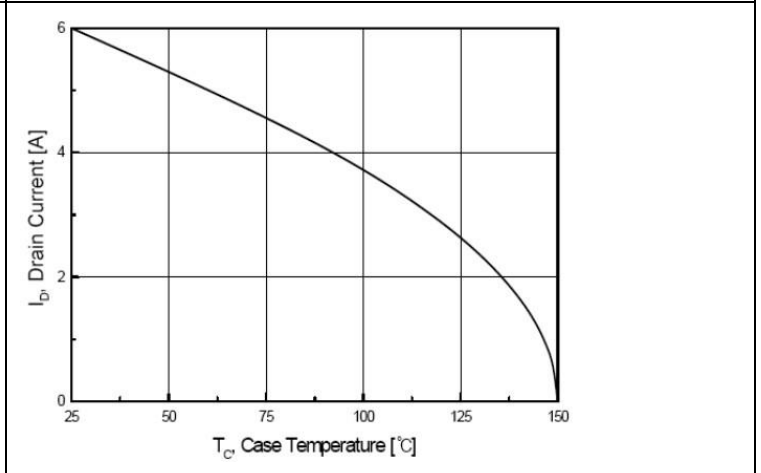


FIG.10-MAXIMUM DRAIN CURRENT VS CASE TEMPERATURE

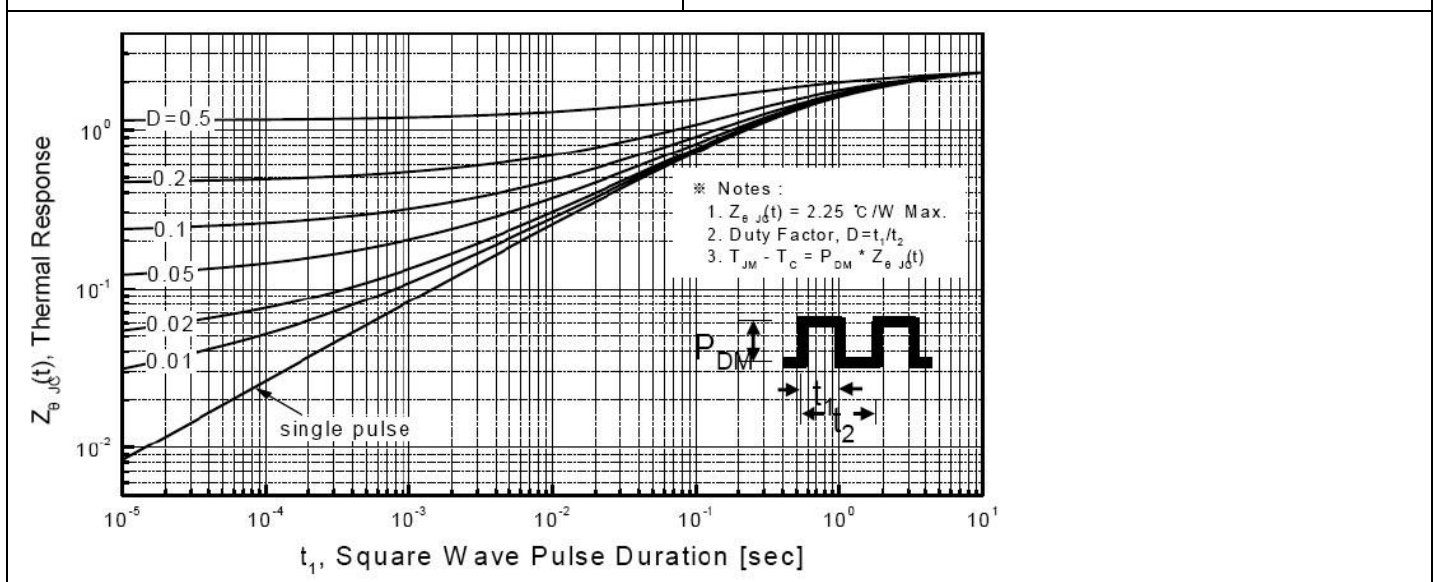


FIG.11-TRANSIENT THERMAL RESPONSE CURVE

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■ Characteristics Test Circuit & Waveform

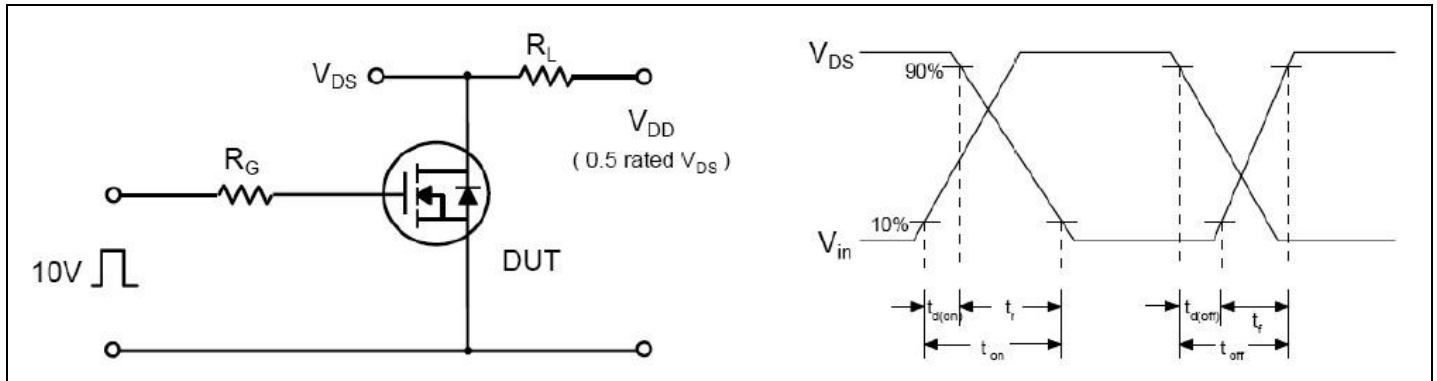


Fig 12. Resistive Switching Test Circuit & Waveforms

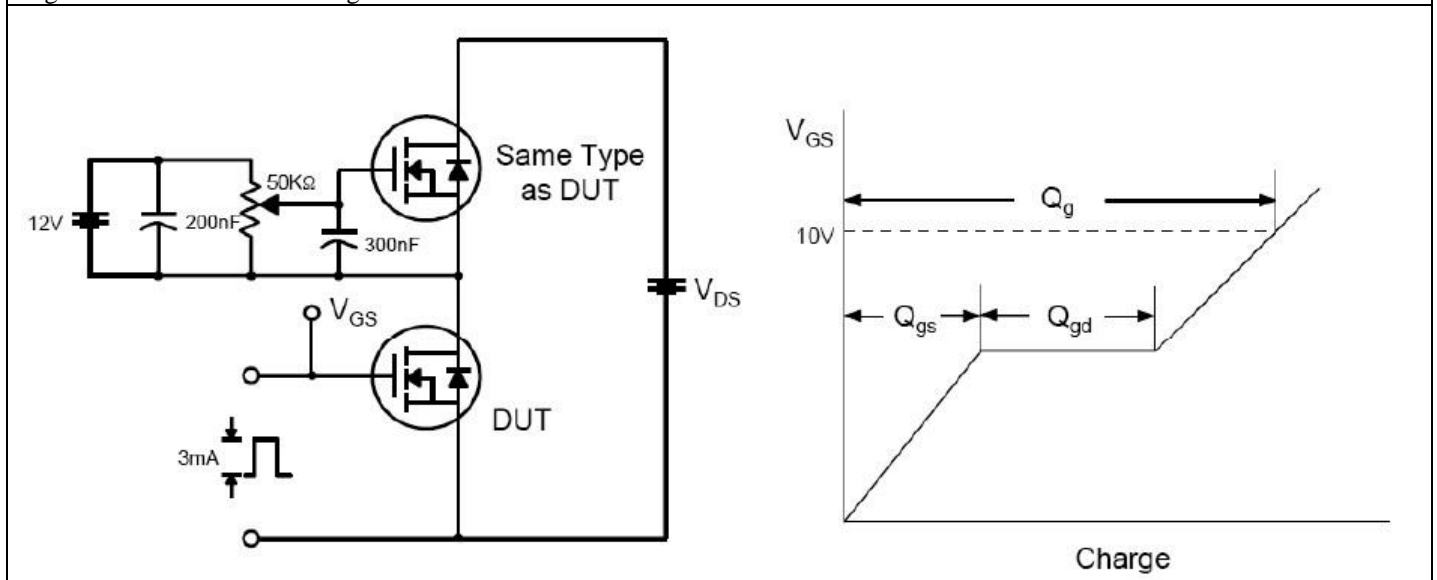


Fig 13. Gate Charge Test Circuit & Waveform

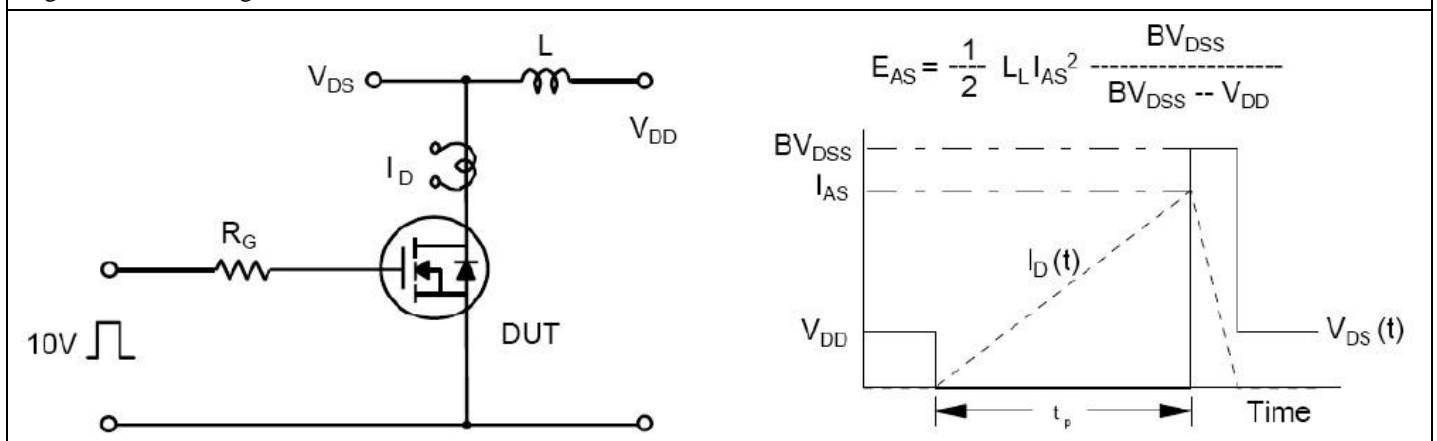


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

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